

**Features**

- $V_{DS} = 30V, I_D = 2A$
- $R_{DS(ON)} < 90m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 120m\Omega @ V_{GS}=4.5V$

**Typical Applications**

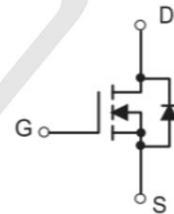
- Load switch
- PWM application

**Shipping Quantity**

- 3000pcs / Tape & Reel



**Circuit Diagram**



N-MOS

**Marking: SYs**

**Absolute Maximum Ratings ( $T_A=25^\circ C$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	2	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	8	A
Maximum Power Dissipation	$P_D$	0.9	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

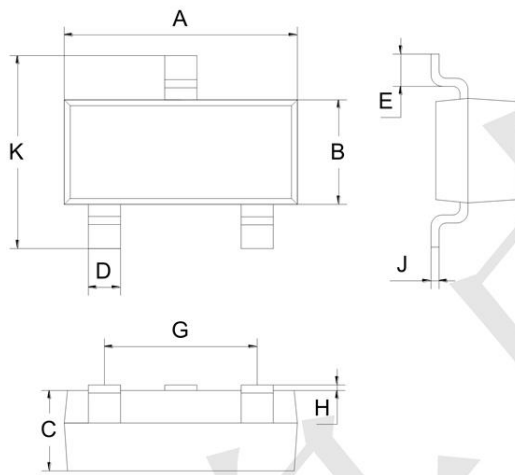
**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	138	$^\circ C/W$
---	-----------------	-----	--------------

**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

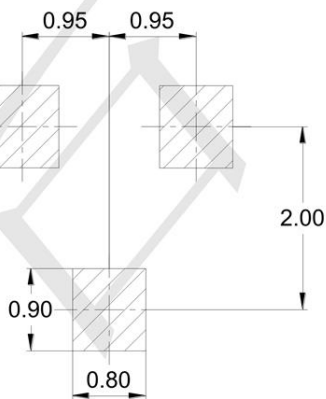
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	3.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2A$	-	-	90	$m\Omega$
		$V_{GS}=4.5V, I_D=2A$	-	-	120	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=2.5A$	14	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	235	-	PF
Output Capacitance	$C_{oss}$		-	35	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	18	-	PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=1A$ $V_{GS}=10V, R_{GEN}=6\Omega$	-	3.5	-	nS
Turn-on Rise Time	$t_r$		-	1.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	17.5	-	nS
Turn-Off Fall Time	$t_f$		-	2.5	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=15V, I_D=2A, V_{GS}=10V$	-	10	-	nC
Gate-Source Charge	$Q_{gs}$		-	0.95	-	nC
Gate-Drain Charge	$Q_{gd}$		-	1.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=2.5A$	-	-	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	2	A

**Outline Drawing - SOT23**



SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

**Land Pattern - SOT23**



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [TECH PUBLIC](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [BUK455-60A/B](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#) [IPS70R2K0CEAKMA1](#) [SQD23N06-31L-GE3](#)  
[TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [DMN1053UCP4-7](#) [SQJ469EP-T1-GE3](#) [NTE2384](#) [DMC2700UDMQ-7](#)  
[DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [DMN2990UFB-7B](#)  
[IPB80P04P405ATMA2](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [MCQ7328-TP](#) [NTMC083NP10M5L](#) [BXP7N65D](#) [BXP4N65F](#) [AOL1454G](#)  
[WMJ80N60C4](#) [BXP2N20L](#) [BXP2N65D](#) [BXT1150N10J](#) [BXT1700P06M](#) [TSM60NB380CP](#) [ROG](#) [RQ7L055BGTGR](#) [DMNH15H110SK3-13](#)  
[SLF10N65ABV2](#) [BSO203SP](#) [BSO211P](#) [IPA60R230P6](#)